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Contents

Preface: Jan Tauc and the optical properties of crystalline and amorphous semiconductors. R. Zallen . vii
Preface: Jan Tauc and the studies of carrier dynamics in amorphous semiconductors. Z.V. Vardeny . . ix
Contents xi

Section 1. Optical properties

Tauc networks and Tauc edges: a review
Phillips, J.C. 1
Urbach edge of crystalline and amorphous silicon: a personal review
Cody, G.D. 3
Review of direct measurements of mobility gaps in a-Si : H using internal photoemission
Wronski, C.R. 16
A review of optical properties of metal chalcogenide glasses
Hautala, J. and P.C. Taylor 24
Optical dephasing in disordered semiconductors
Göbel, E.O. and P. Thomas 35
Magnetic field effects in optically encoded second harmonic generation in germanosilicate glasses
Lawandy, N.M. and R.L. MacDonald 47
The structure of silicon- and germanium-based alloys by X-ray absorption spectroscopy
Evangelisti, F. 53
Wide-frequency dielectric susceptibility measurements in glycerol
Menon, N., K.P. O'Brien, P.K. Dixon, L. Wu, S.R. Nagel, B.D. Williams and J.P. Carini 61

Section 2. Photoexcitations

Studies of photocarrier relaxation processes in polysilane alloys from subpicosecond to metastability
Verdeny, Z.V., X. Wei, B.C. Hess, S.G. Han and S. Nita 66
The properties of free carriers in amorphous silicon
Fauchet, P.M., D. Hulin, R. Vanderhaghen, A. Mourchid and W.L. Nighan, Jr. 76
The puzzle surrounding luminescence models
Kemp, M. and M. Silver 88
Excitonic states in hydrogenated amorphous silicon
Stutzmann, M. and M.S. Brandt 97

Section 3. Optical probes of transport

Optically detected photocarrier transport in amorphous silicon: a review
Devlen, R.I. and E.A. Schiff 106
Determination of surface recombination velocity of excess carriers in amorphous silicon using the SSPG technique
Haridim, M., E. Kurin, K. Weiser and H. Mell 119

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Some observations on the photoconductivity of amorphous semiconductors
Fritzsche, H., B.-G. Yoon, D.-Z. Chi and M.Q. Tran 123
Phototransport in a-Si:H at high electric fields
Kočka, J., O. Klíma, E. Šípek and G. Juška 133
Deep defect structure and carrier dynamics in amorphous silicon and silicon–germanium alloys determined by transient photocapacitance methods
Cohen, J.D., T. Unold, A.V. Gelatos and C.M. Fortmann 142
Study of the deep-states density by time-resolved transient photocurrent measurements
Nesládek, M., A. Tříska and G.J. Adriaenssens 155

Section 4. Metastable optical effects

Time-of-flight measurements of thermally induced defects in a-Si–H
Street, R.A. and C.C. Tsai 162
Self-trapping of holes and light- and thermally induced defect creation in a-Si:H
Morigaki, K. 166
Light-induced defects in phosporus-doped hydrogenated amorphous silicon
Okushi, H., S. Yamasaki and K. Tanaka 176
Light-induced changes in the DOS of chalcogenide glasses studied by xerographic techniques
Abkowitz, M.A. 188
Optically induced phase changes in amorphous materials
Ovshinsky, S.R. 200
The saturation of light-induced defects in hydrogenated amorphous silicon
Isomura, M. and S. Wagner 204

Section 5. Optical probes of nanostructures

Investigation of amorphous Si superlattices by electroabsorption: a review
Hattori, K., H. Okamoto and Y. Hamakawa 216
Optical studies of nanocrystalline GaAs: a review
Zallen, R. 227
Finite size effects on the dynamics of amorphous and nanocrystalline materials
Lannin, J.S. 233

Section 6. Optical probes of vibrational and structural properties

Hydrogen in amorphous silicon: local bonding and vibrational properties
Lucovsky, G. 241
Isotope effects on the electronic excitations and phonons in semiconductors
Cardona, M., C.H. Grein, H.D. Fuchs and S. Zollner 257
Transverse acoustic phonons in amorphous silicon
Thomsen, C. and E. Bustarret 265
Structural properties of amorphous hydrogenated germanium
Paul, W., S.J. Jones, W.A. Turner and P. Wickboldt 271

Author index 287
Subject index 289